

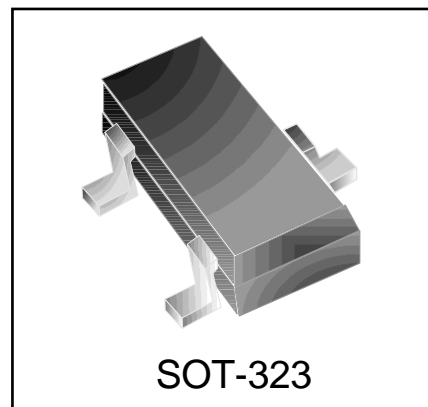
## N-Channel Trench MOSFET

### Features

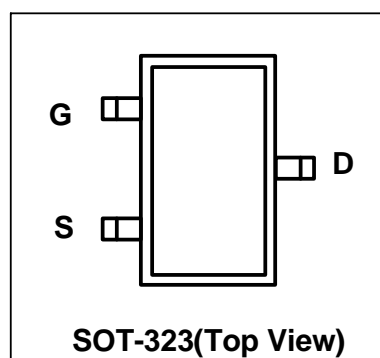
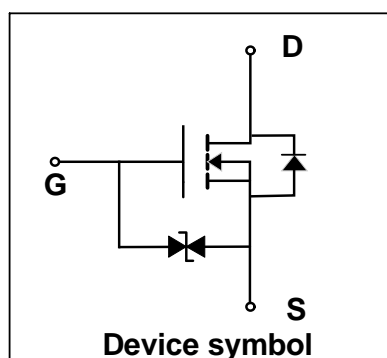
- $V_{DS} = 30V$ ,  $I_D = 0.1A$   
 $R_{DS(on)} < 3\Omega @ V_{GS} = 4.5V$   
 $R_{DS(on)} < 4\Omega @ V_{GS} = 2.5V$
- Very Fast Switching
- Trench MOSFET Technology
- Low Threshold Voltage
- Pb Free Device
- ESD Protected

### Mechanical Characteristics

- SOT-323 Package
- Marking : Making Code
- RoHS Compliant



### Schematic & PIN Configuration



### Absolute Maximum Rating

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	100	mA
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	300	mA
Power Dissipation	$P_D$	200	mW
Junction Temperature	$T_J$	150	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 to +150	$^{\circ}C$
Thermal Resistance from Junction to Ambient <sup>2</sup>	$R_{\theta JA}$	625	$^{\circ}C/W$

**Electrical Characteristics** ( $T_{amb}=25^{\circ}\text{C}$  unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 5$	$\mu A$
Gate Threshold Voltage <sup>3</sup>	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.7	-	1.4	V
Drain-Source on-State Resistance <sup>3</sup>	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 10mA$	-	1	3	$\Omega$
		$V_{GS} = 2.5V, I_D = 1mA$	-	1.9	4	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 5V,$ $f = 1MHz$	-	30	-	pF
Output Capacitance	$C_{oss}$		-	7.7	-	
Reverse Transfer Capacitance	$C_{rss}$		-	3.5	-	
<b>Switching Characteristics</b>						
Turn-on Delay Time <sup>4</sup>	$t_{d(on)}$	$V_{GS} = 5V, V_{DD} = 10V,$ $R_L = 500\Omega, R_{GEN} = 10\Omega$	-	15	-	nS
Turn-on Rise Time <sup>4</sup>	$t_r$		-	35	-	
Turn-off Delay Time <sup>4</sup>	$t_{d(off)}$		-	80	-	
Turn-off Fall Time <sup>4</sup>	$t_f$		-	80	-	
<b>Drain-Source Body Diode Characteristics</b>						
Body Diode Voltage	$V_{SD}$	$I_S = 0.1A, V_{GS} = 0V$	-	-	1.4	V

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface mounted on FR4 board using 1 square inch pad size, 1oz single-side copper.
3. Pulse Test: Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to product

Typical Characteristics

Figure 1. Output Characteristics

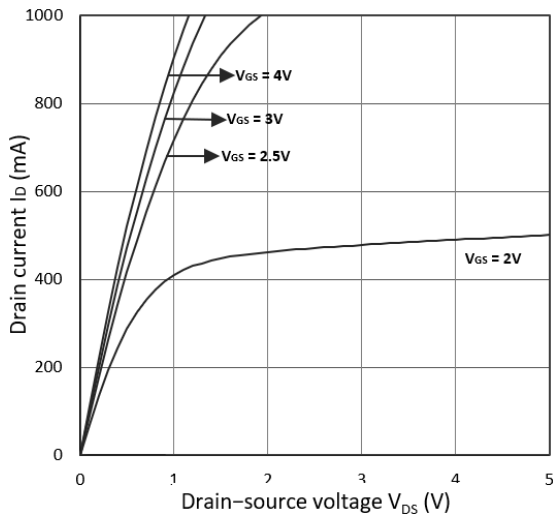


Figure 3.  $R_{DS(ON)}$  vs.  $I_D$

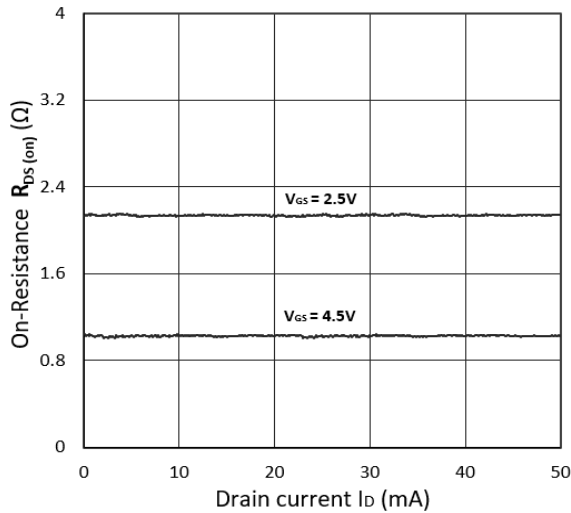


Figure 5.  $I_S$  vs.  $V_{SD}$

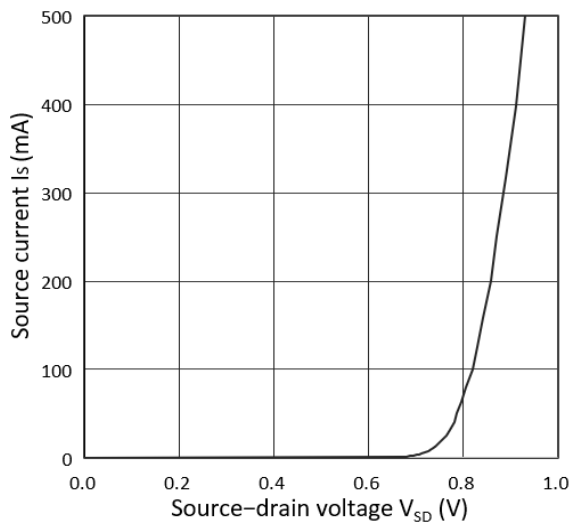


Figure 2. Transfer Characteristics

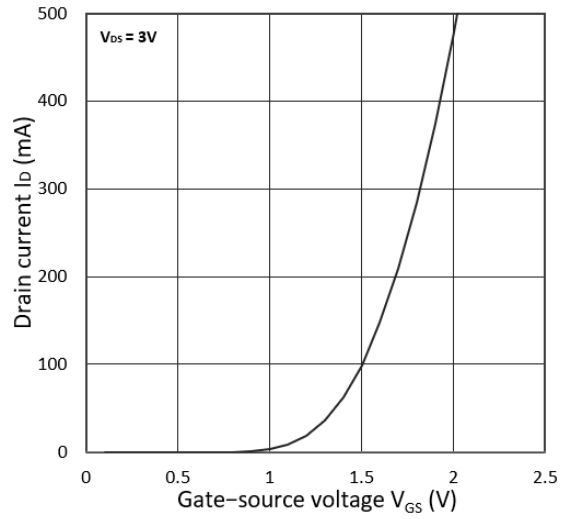


Figure 4.  $R_{DS(ON)}$  vs.  $V_{GS}$

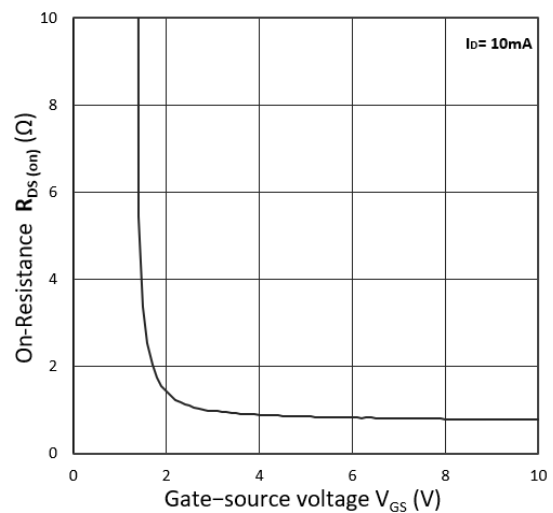
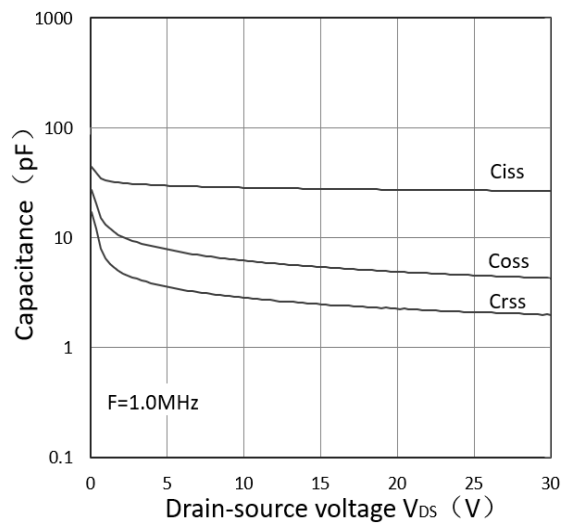


Figure 6. Capacitance Characteristics



Outline Drawing – SOT-323

### PACKAGE OUTLINE

**SOT-323**

DIMENSIONS				
SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
D	2.000	2.200	0.079	0.087
b	0.300	0.500	0.012	0.020
c	0.100	0.150	0.004	0.006
E	2.150	2.450	0.085	0.096
E1	1.150	1.350	0.045	0.053
e	0.650TYP		0.026TYP	
L	0.525 REF		0.021 REF	
θ	0	8°	0	8°

DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.076	1.90
C	0.036	0.9
Z	0.108	2.7
e	0.026	0.65
e1	0.052	1.30
b	0.028	0.7

**Notes**

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM03N01G
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

No.1001, Shiwan (7) Road, Pudong District, Shanghai, P.R.China.201207

Tel: 86-21-68969993 Fax: 86-21-50757680 Email: [market@way-on.com](mailto:market@way-on.com)

WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

**WAYON**® is registered trademark of Wayon Corporation.

Specifications are subject to change without notice.  
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.  
Users should verify actual device performance in their specific applications.

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [Wayon](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)  
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)  
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)  
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [NTMC083NP10M5L](#) [NVMFS2D3P04M8LT1G](#) [BXP7N65D](#)  
[BXP4N65F](#) [AOL1454G](#) [WMJ80N60C4](#) [BXP2N20L](#) [BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTCR](#)  
[DMNH15H110SK3-13](#) [SLF10N65ABV2](#) [BSO203SP](#) [BSO211P](#)